FDD3860

N-Channel PowerTrench® MOSFET

100V, 29A, 36mΩ

Features

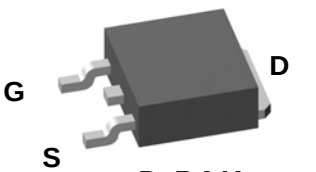
- Max $r_{DS(on)}$ = 36mΩ at V_{GS} = 10V, I_D = 5.9A
- High performance trench technology for extremely low $r_{DS(on)}$
- 100% UIL tested
- RoHS Compliant

General Description

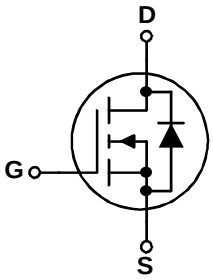
This N-Channel MOSFET is rugged gate version of Fairchild Semiconductor's advanced Power Trench® process. This part is tailored for low $r_{DS(on)}$ and low Qg figure of merit, with avalanche ruggedness for a wide range of switching applications.

Applications

- DC-AC Conversion
- Synchronous Rectifier



D-PAK
(TO-252)



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			100	V
V_{GS}	Gate to Source Voltage			±20	V
I_D	Drain Current -Continuous (Silicon limited)	T_C = 25°C		29	A
	-Continuous	T_A = 25°C	(Note 1a)	6.2	
	-Pulsed			60	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	121	mJ
P_D	Power Dissipation	T_C = 25°C		69	W
	Power Dissipation	T_A = 25°C	(Note 1a)	3.1	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	40	

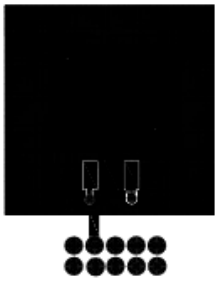
Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD3860	FDD3860	D-PAK (TO-252)	13"	12mm	2500 units

Electrical Characteristics T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		98		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80V, V_{GS} = 0V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	2.5	3.8	4.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250μA, referenced to 25°C		-11.4		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10V, I_D = 5.9A		29	36	mΩ
		V_{GS} = 10V, I_D = 5.9A, T_J = 125°C		51	64	
g_{FS}	Forward Transconductance	V_{DS} = 10V, I_D = 5.9A		20		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 50V, V_{GS} = 0V, f = 1MHz		1310	1740	pF
C_{oss}	Output Capacitance			100	130	pF
C_{rss}	Reverse Transfer Capacitance			45	70	pF
R_g	Gate Resistance	f = 1MHz		1.6		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50V, I_D = 5.9A, V_{GS} = 10V, R_{GEN} = 6Ω		16	29	ns
t_r	Rise Time			10	21	ns
$t_{d(off)}$	Turn-Off Delay Time			24	39	ns
t_f	Fall Time			7	15	ns
Q_g	Total Gate Charge at 10V	V_{DD} = 50V, I_D = 5.9A		22	31	nC
Q_{gs}	Gate to Source Charge			7.1		nC
Q_{gd}	Gate to Drain “Miller” Charge			6.3		nC
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0V, I_S = 2.0A (Note 2)		0.7	1.2	V
		V_{GS} = 0V, I_S = 5.9A (Note 2)		0.8	1.3	
t_{rr}	Reverse Recovery Time	I_F = 5.9A, di/dt = 100A/μs		34	55	ns
Q_{rr}	Reverse Recovery Charge			40	64	nC

Notes:
1: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.



a) 40°C/W when mounted on a 1 in^2 pad of 2 oz copper

b) 96°C/W when mounted on a minimum pad.

2: Pulse Test: Pulse Width < 300μs, Duty cycle < 2.0%.
3: Starting T_J = 25°C, L = 3mH, I_{AS} = 9A, V_{DD} = 100V, V_{GS} = 10V.

Typical Characteristics T_J = 25°C unless otherwise noted

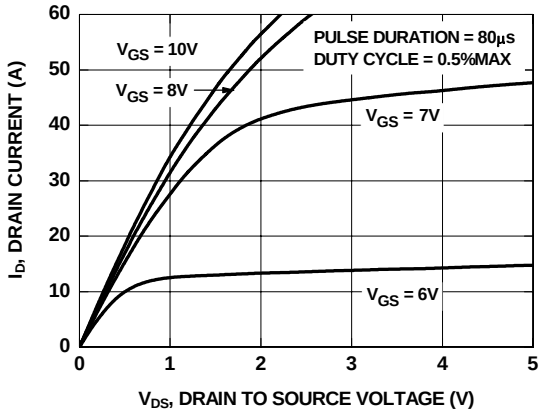


Figure 1. On-Region Characteristics

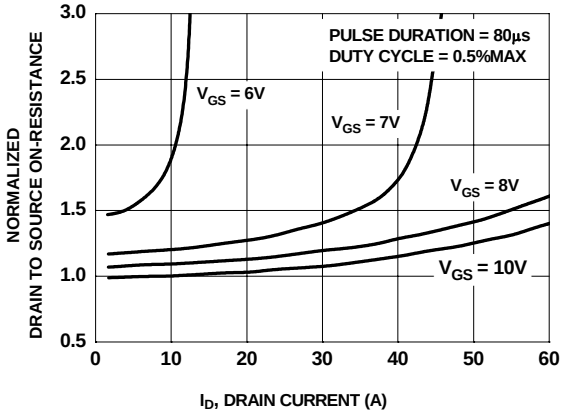


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

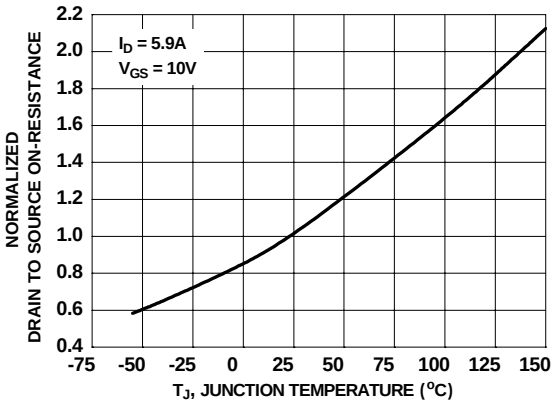


Figure 3. Normalized On-Resistance vs Junction Temperature

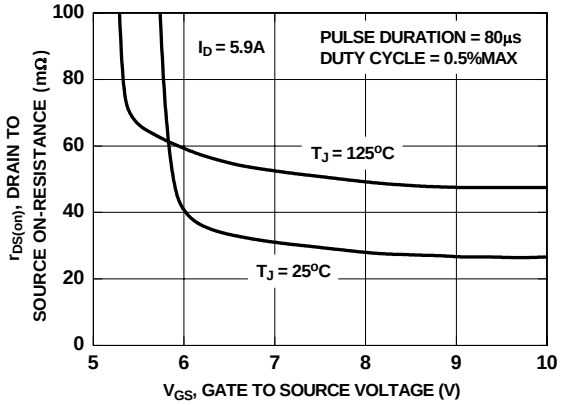


Figure 4. On-Resistance vs Gate to Source Voltage

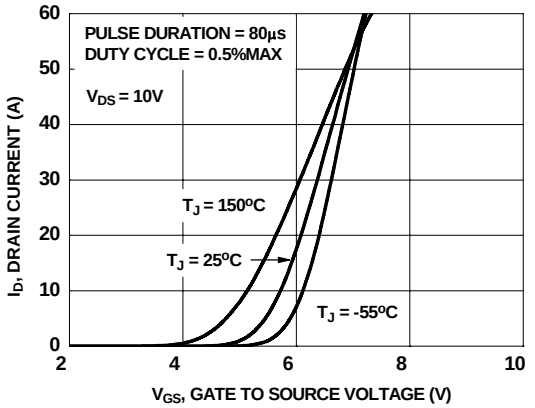


Figure 5. Transfer Characteristics

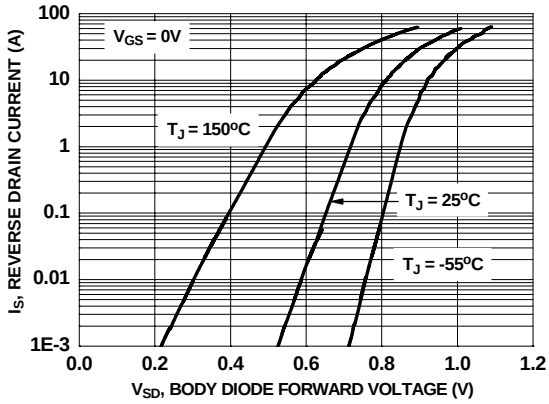


Figure 6. Source to Drain Diode Forward Voltage vs Source Current